Ordering number:EN2828

NPN Triple Diffused Planar Silicon Transistor

2SC3994

800V/25A Switching Regulator Applications

Features

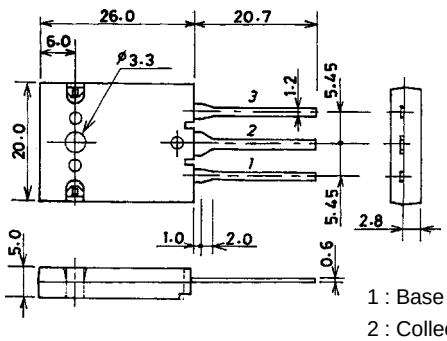
- High breakdown voltage, high reliability.
- Fast switching speed (t_f=0.1μs typ).
- Wide ASO.
- Adoption of MBIT process.

Package Dimensions

unit:mm

2048B

[2SC3994]



1 : Base
2 : Collector
3 : Emitter
SANYO : TO-3PBL

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		1100	V
Collector-to-Emitter Voltage	V_{CEO}		800	V
Emitter-to-Base Voltage	V_{EBO}		7	V
Collector Current	I_C		25	A
Collector Current (Pulse)	I_{CP}	PW≤300μs, duty cycle≤10%	60	A
Base Current	I_B		12	A
Collector Dissipation	P_C	Tc=25˚C	300	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=800V, I_E=0			10	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=5V, I_C=0			10	μA
DC Current Gain	$h_{FE}1$*	V_{CE}=5V, I_C=1.6A	10		40	
	$h_{FE}2$	V_{CE}=5V, I_C=8A	8			
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=1.6A		15		MHz
Output Capacitance	C_{ob}	V_{CB}=10V, f=1MHz		470		pF

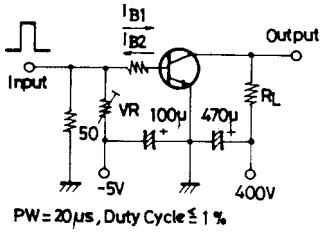
* : The $h_{FE}1$ of the 2SC3994 is classified as follows. When specifying the $h_{FE}1$ rank, specify two ranks or more in principle.

10 K 20	15 L 30	20 M 40

SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

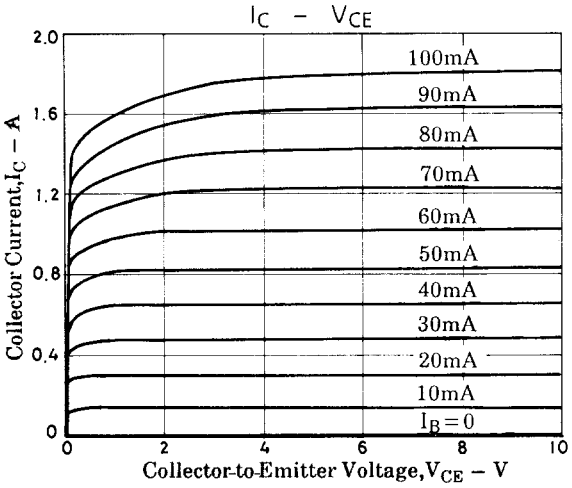
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=12A, I_B=2.4A			2.0	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=12A, I_B=2.4A			1.5	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=1mA, I_E=0	1100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=10mA, R_{BE}=∞	800			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	7			V
Collector-to-Emitter Sustain Voltage	$V_{CEX(sus)}$	I_C=12A, I_{B1}=–I_{B2}=–2.4A, L=50μH, clamped	800			V
Turn-ON Time	t_{on}	V_{CC}=400V, 5I_{B1}=–2.5I_{B2}=I_C=20A, R_L=20Ω			0.5	μs
Storage Time	t_{stg}	V_{CC}=400V, 5I_{B1}=–2.5I_{B2}=I_C=20A, R_L=20Ω			3.0	μs
Fall Time	t_f	V_{CC}=400V, 5I_{B1}=–2.5I_{B2}=I_C=20A, R_L=20Ω			0.3	μs

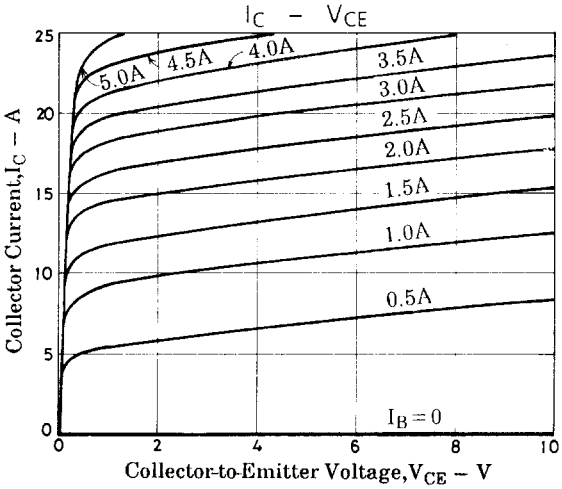
Switching Time Test Circuit

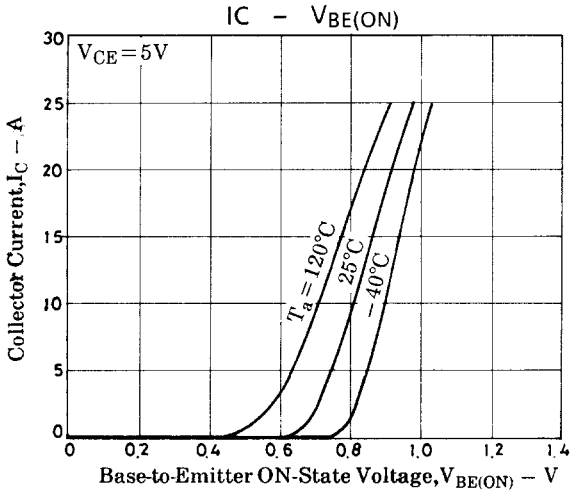


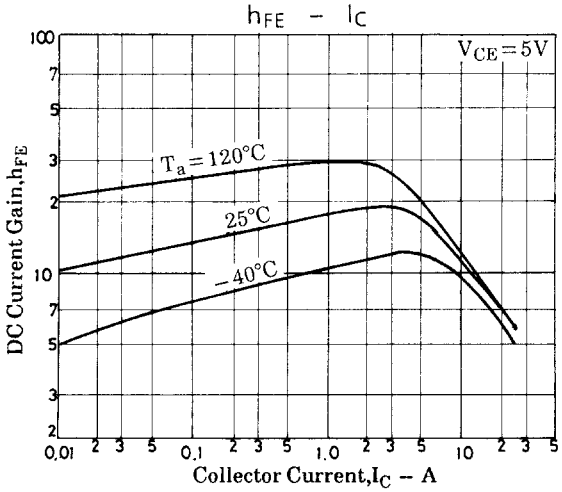
PW=20μs, Duty Cycle≦1%

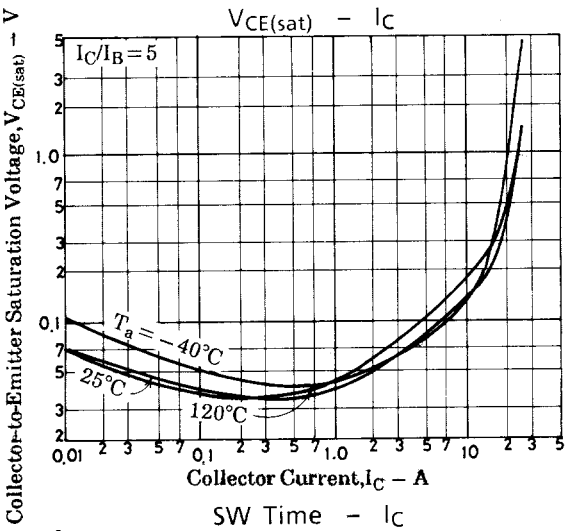
Unit (resistance : Ω, capacitance : F)

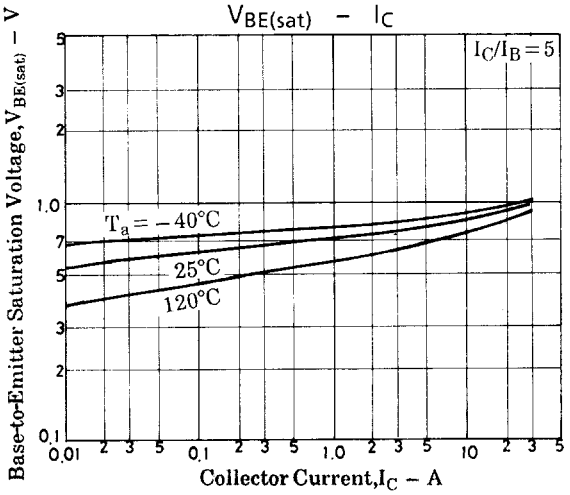


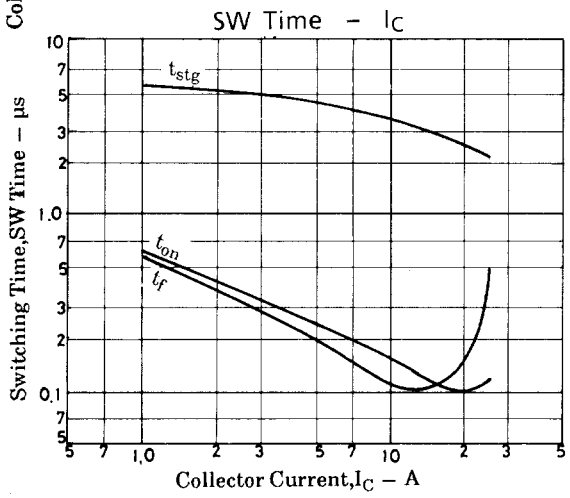


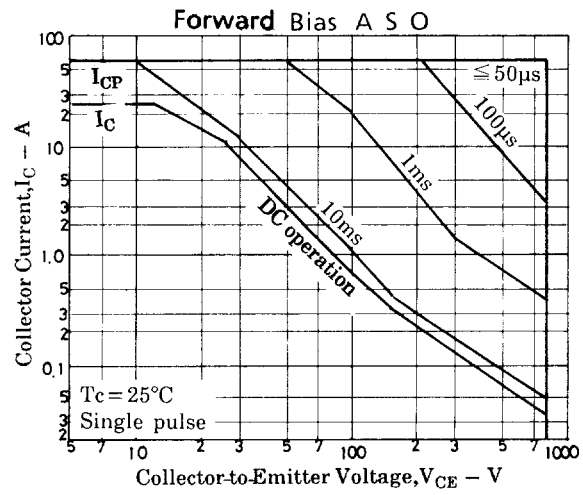


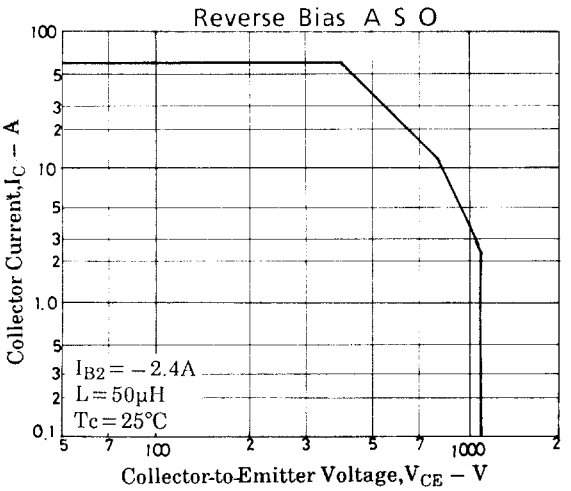


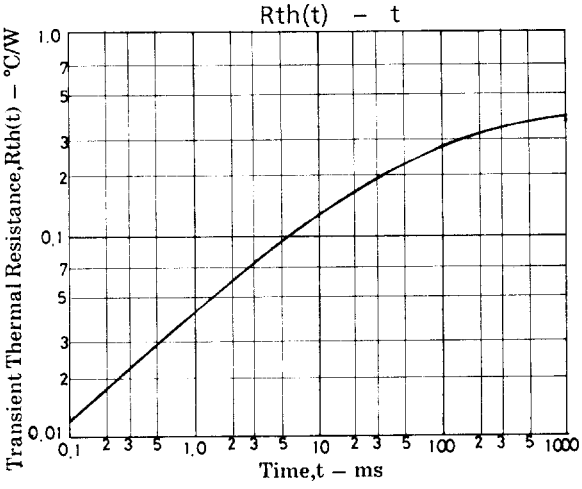

VCE(sat) – IC
IC/IB=5
Ta=–40°C
25°C
120°C
Collector-to-Emitter Saturation Voltage,VCE(sat) – V
Collector Current,IC – A


VBE(sat) – IC
IC/IB=5
Ta=–40°C
25°C
120°C
Base-to-Emitter Saturation Voltage,VBE(sat) – V
Collector Current,IC – A


SW Time – IC
tstg
ton
tf
Switching Time,SW Time – µs
Collector Current,IC – A


Forward Bias A S O
ICP
IC
≦50µs
100µs
1ms
10ms
DC operation
Tc=25°C
Single pulse
Collector Current,IC – A
Collector-to-Emitter Voltage,VCE – V


Reverse Bias A S O
IB2=–2.4A
L=50µH
Tc=25°C
Collector Current,IC – A
Collector-to-Emitter Voltage,VCE – V


Rth(t) – t
Transient Thermal Resistance,Rth(t) – °C/W
Time,t – ms